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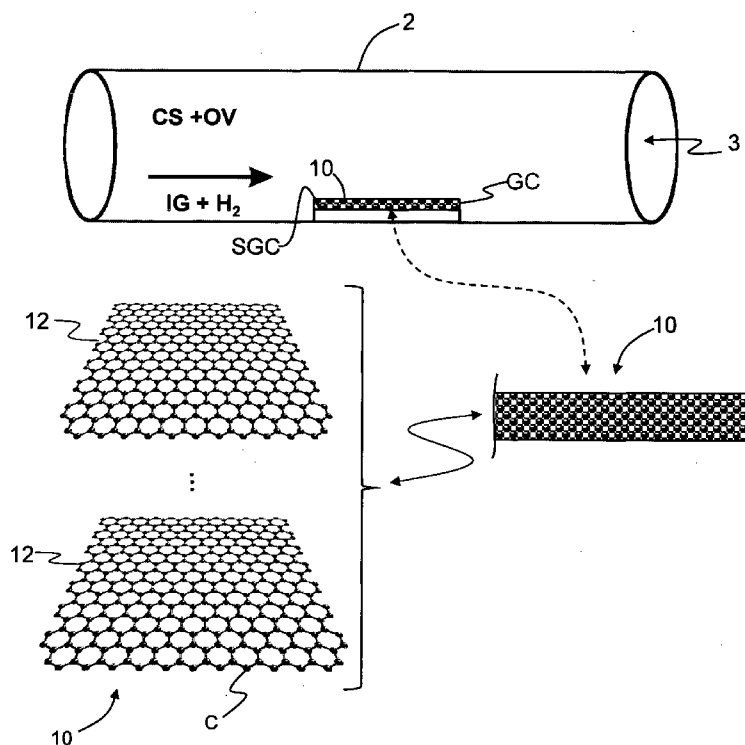
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(54) Title: METHODS OF GROWING UNIFORM, LARGE-SCALE, MULTILAYER GRAPHENE FILMS



(57) Abstract: Methods of growing a multilayer graphene film (10) include flowing a weak oxidizing vapor (OV) and a gaseous carbon source (CS) over a surface (SGC) of a carbonizing catalyst (GC) in a CVD reaction chamber (2). Carbon atoms (C) deposit on the carbonizing catalyst surface to form sheets of single-layer graphene (12) upon cooling. The method generates a substantially uniform stacking of graphene layers to form the multilayer graphene film. The multilayer graphene film is substantially uniform and has a relatively large scale as compared to graphene films formed by prior-art methods.



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— *with international search report (Art. 21(3))*

Declarations under Rule 4.17:

— *of inventorship (Rule 4.17(iv))*